

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild <a href="general-regarding-numbers-n

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



June 2014

FDMA910PZ

Single P-Channel PowerTrench® MOSFET -20 V, -9.4 A, 20 m Ω

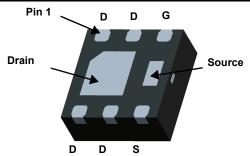
Features

- Max $r_{DS(on)}$ = 20 m Ω at V_{GS} = -4.5 V, I_D = -9.4 A
- Max $r_{DS(on)}$ = 24 m Ω at V_{GS} = -2.5 V, I_D = -8.6 A
- Max $r_{DS(on)}$ = 34 m Ω at V_{GS} = -1.8 V, I_D = -7.2 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x2 mm
- HBM ESD protection level > 2.8k V typical (Note 3)
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

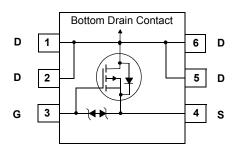
General Description

This device is designed specifically for battery charge or load switching in cellular handset and other ultraportable applications. It features a MOSFET with low on-state resistance and zener diode protection against ESD. The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.









MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Param	eter		Ratings	Units
V_{DS}	Drain to Source Voltage			-20	V
V_{GS}	Gate to Source Voltage			±8	V
	-Continuous	T _A = 25°C	(Note 1a)	-9.4	^
'D	-Pulsed			-45	Α
D	Power Dissipation	T _A = 25°C	(Note 1a)	2.4	10/
P_{D}	Power Dissipation	T _A = 25°C	(Note 1b)	0.9	W
T _J , T _{STG}	Operating and Storage Junction Tempera	ature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
910	FDMA910PZ	MicroFET 2X2	7"	8 mm	3000 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, referenced to 25 °C		-12		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16 V, V _{GS} = 0 V			-1	μА
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±1	μΑ

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250 \mu A$	-0.4	-0.5	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25 °C		3		mV/°C
	$V_{GS} = -4.5 \text{ V}, I_D = -9.4 \text{ A}$		16	20		
		$V_{GS} = -2.5 \text{ V}, I_D = -8.6 \text{ A}$		19	24	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = -1.8 \text{ V}, I_D = -7.2 \text{ A}$		24	34	mΩ
	$V_{GS} = -4.5 \text{ V}, I_D = -9.4 \text{ A},$ $T_J = 125 ^{\circ}\text{C}$		20	25		
9 _{FS}	Forward Transconductance	$V_{DD} = -5 \text{ V}, I_{D} = -9.4 \text{ A}$		52		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 40 V V - 0 V	2110	2805	pF
Coss	Output Capacitance	─V _{DS} = -10 V, V _{GS} = 0 V, —f = 1 MHz	414	620	pF
C _{rss}	Reverse Transfer Capacitance	1 1 1411 12	388	580	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		9.4	19	ns
t _r	Rise Time	V_{DD} = -10 V, I_{D} = -9.4 A, V_{GS} = -4.5 V, R_{GEN} = 6 Ω	19	34	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = -4.5 V, R _{GEN} = 6 12	135	216	ns
t _f	Fall Time		103	165	ns
Q_g	Total Gate Charge	V _{GS} = -4.5 V, V _{DD} = -10 V,	21	29	nC
Q_{gs}	Gate to Source Charge	I _D = -9.4 A	2.5		nC
Q_{gd}	Gate to Drain "Miller" Charge		6		nC

Drain-Source Diode Characteristics

Tyon 15001ce to Drain Diode Forward Voltage	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -2 \text{ A}$ (Note 2)		-0.6	-0.6 -1.2	V
	$V_{GS} = 0 \text{ V}, I_{S} = -9.4 \text{ A}$ (Note 2)		-0.8	-1.2	٧	
t _{rr}	Reverse Recovery Time	-I _F = -9.4 A, di/dt = 100 A/μs		23	37	ns
Q _{rr}	Reverse Recovery Charge			6.3	13	nC

NOTES

^{1.} R_{0,JA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0,JC} is guaranteed by design while R_{0,JA} is determined by the user's board design.



a. 52 °C/W when mounted on a 1 in² pad of 2 oz copper.



 b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.
- 3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics T_J = 25 °C unless otherwise noted

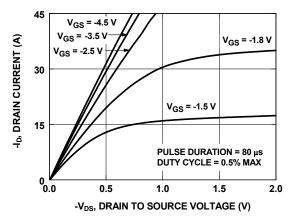


Figure 1. On-Region Characteristics

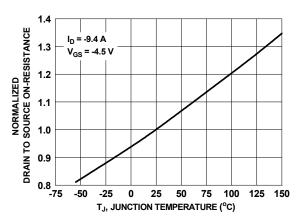


Figure 3. Normalized On-Resistance vs Junction Temperature

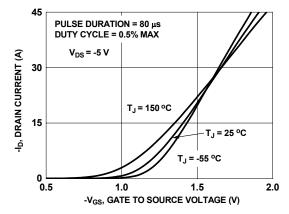


Figure 5. Transfer Characteristics

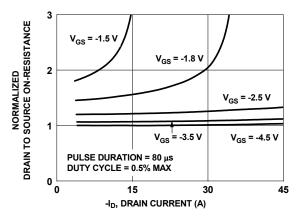


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

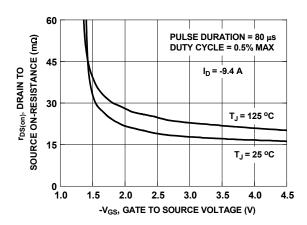


Figure 4. On-Resistance vs Gate to Source Voltage

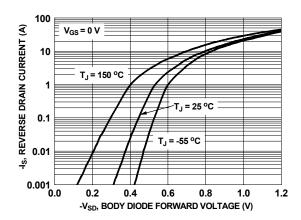


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

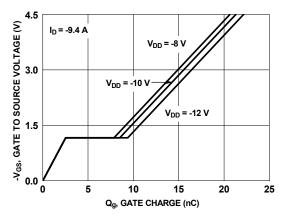


Figure 7. Gate Charge Characteristics

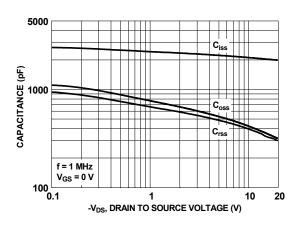


Figure 8. Capacitance vs Drain to Source Voltage

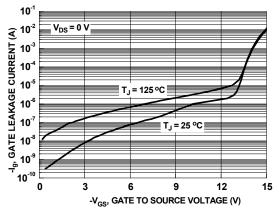


Figure 9. Gate Leakage Current vs Gate to Source Voltage

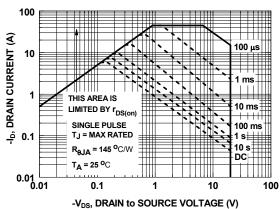


Figure 10. Forward Bias Safe
Operating Area

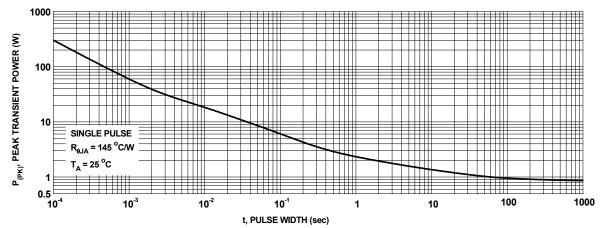


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

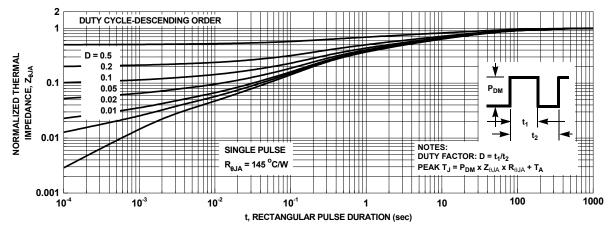
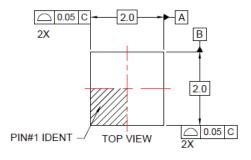
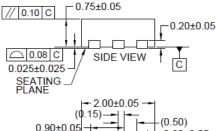
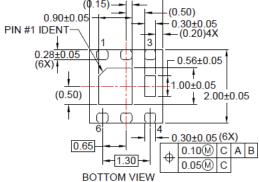


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout

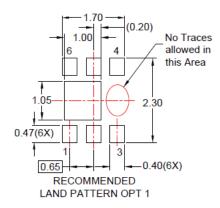


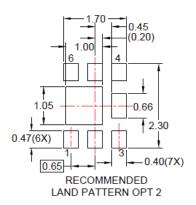




NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP06Lrev4.







Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_MLDEB-C06





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
AX-CAP[®]*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™

Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™

Fairchild®

Fairchild Semiconductor[®]
FACT Quiet Series™
FACT[®]
FAST[®]
FastvCore™
FETBench™
FPS™

F-PFS™ FRFET®

Global Power ResourceSM GreenBridge[™] Green FPS[™] Green FPS[™] e-Series[™]

Gmax[™] GTO[™] IntelliMAX[™]

ISOPLANAR™ Marking Small Speakers Sound Louder

and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
mWSaver®
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®

®
PowerTrench®
PowerXS™

Programmable Active Droop™

QFET® QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™

SPM®
STEALTH™
SUPERFET®
SUPERSOT™-3
SUPERSOT™-6
SUPERSOT™-8
SUPERSOT™-8
SUPERSOT™-8
SYNCFET™
SYNC-LOCK™

SYSTEM ®*
GENERAL
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TiNYOPTO™
TinyPOWET™
TinyPWM™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®**
µSerDes™

SerDes"
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
从S™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN. WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

EAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are
 intended for surgical implant into the body or (b) support or sustain life,
 and (c) whose failure to perform when properly used in accordance with
 instructions for use provided in the labeling, can be reasonably
 expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information Formative / In Design		Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed Full Production		Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete Not In Production		Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I68

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and h

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative